

isc Silicon NPN Power Transistor

BU2527AF

DESCRIPTION

- Collector-Emitter Sustaining Voltage-  
:  $V_{CEO(SUS)} = 800V$  (Min)
- High Switching Speed

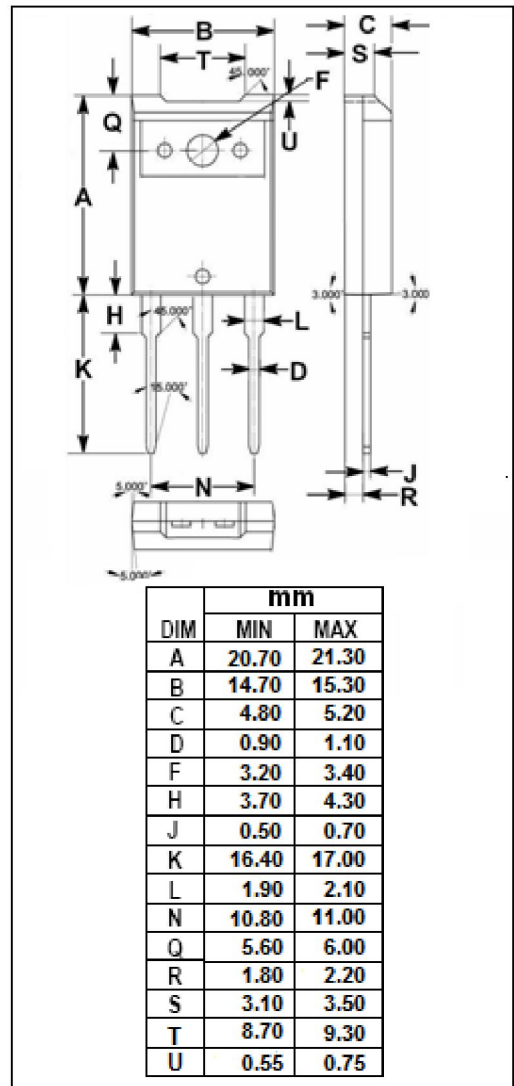
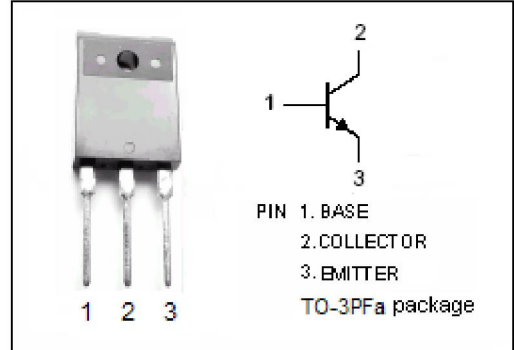
APPLICATIONS

- Designed for use in horizontal deflection circuits of high resolution monitors.

ABSOLUTE MAXIMUM RATINGS( $T_a=25^{\circ}C$ )

SYMBOL	PARAMETER	VALUE	UNIT
$V_{CES}$	Collector- Emitter Voltage( $V_{BE} = 0$ )	1500	V
$V_{CEO}$	Collector-Emitter Voltage	800	V
$V_{EBO}$	Emitter-Base Voltage	7.5	V
$I_C$	Collector Current- Continuous	12	A
$I_{CM}$	Collector Current-Peak	30	A
$I_B$	Base Current- Continuous	8	A
$I_{BM}$	Base Current-Peak	12	A
$P_C$	Collector Power Dissipation @ $T_C=25^{\circ}C$	45	W
$T_J$	Junction Temperature	150	$^{\circ}C$
$T_{stg}$	Storage Temperature Range	-65~150	$^{\circ}C$

SYMBOL	PARAMETER	MAX	UNIT
$R_{th j-c}$	Thermal Resistance, Junction to Case	2.8	$^{\circ}C/W$



**isc Silicon NPN Power Transistor****BU2527AF****ELECTRICAL CHARACTERISTICS** $T_C=25^{\circ}\text{C}$  unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{CEO(SUS)}$	Collector-Emitter Sustaining Voltage	$I_C=100\text{mA}; I_B=0, L=25\text{mH}$	800			V
$V_{(BR)EBO}$	Emitter-Base Breakdown Voltage	$I_E=1\text{mA}; I_C=0$	7.5			V
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	$I_C=6\text{A}; I_B=1.2\text{A}$			5.0	V
$V_{BE(sat)}$	Base-Emitter Saturation Voltage	$I_C=6\text{A}; I_B=1.2\text{A}$			1.3	V
$I_{CES}$	Collector Cutoff Current	$V_{CE}=1500\text{V}; V_{BE}=0$ $V_{CE}=1500\text{V}; V_{BE}=0; T_C=125^{\circ}\text{C}$			0.25 2.0	mA
$I_{EBO}$	Emitter Cutoff Current	$V_{EB}=7.5\text{V}; I_C=0$			0.25	mA
$h_{FE-1}$	DC Current Gain	$I_C=1\text{A}; V_{CE}=5\text{V}$		10		
$h_{FE-2}$	DC Current Gain	$I_C=6\text{A}; V_{CE}=5\text{V}$	5		9	
$C_{OB}$	Output Capacitance	$I_E=0; V_{CB}=10\text{V}; f_{test}=1\text{MHz}$		145		pF